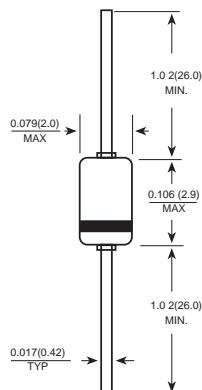


1N4148

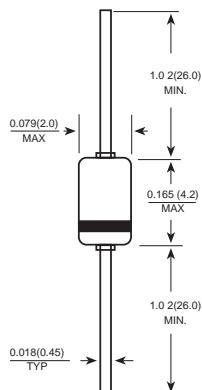
SMALL SIGNAL SWITCHING DIODE

DO-34(GLASS)



Dimensions in inches and (millimeters)

DO-35(GLASS)



FEATURES

- ◆ Silicon epitaxial planar diode
- ◆ Switching diodes
- ◆ 500mw power dissipation
- ◆ High temperature soldering guaranteed
250°C/10 seconds, 0.375" (9.5mm) lead length,
5 lbs. (2.3kg) tension

MECHANICAL DATA

Case: DO-34\DO-35 glass sealed envelope.

Terminals: Plated axial leads, solderable per MIL-STD-750, Method 2026

Polarity: Color band denotes cathode end

Mounting Position: Any

Weight: 0.003 ounce, 0.09 grams(DO-34)
0.005 ounce, 0.14 grams(DO-35)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

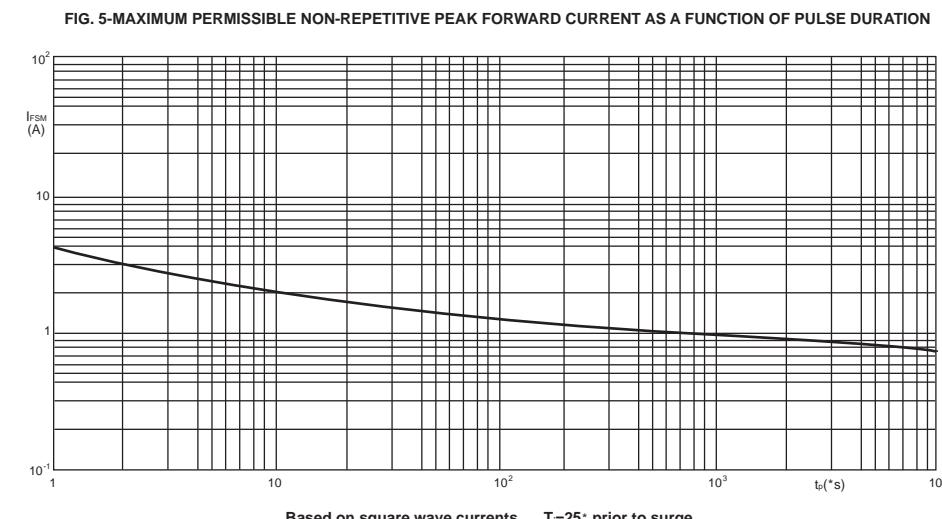
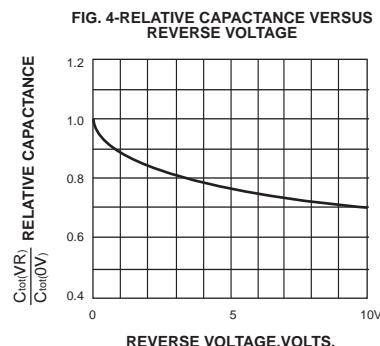
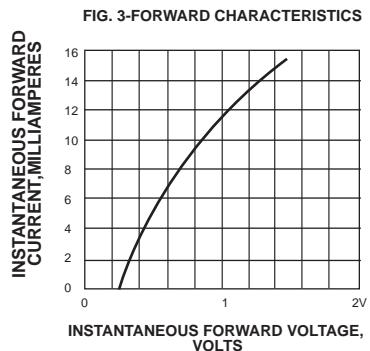
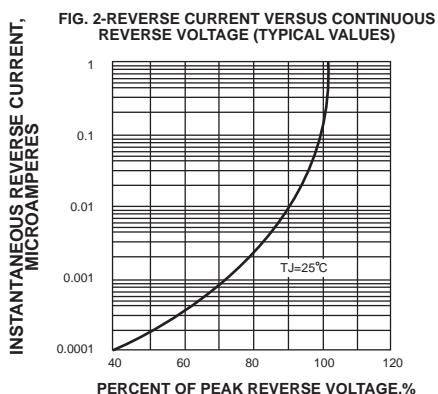
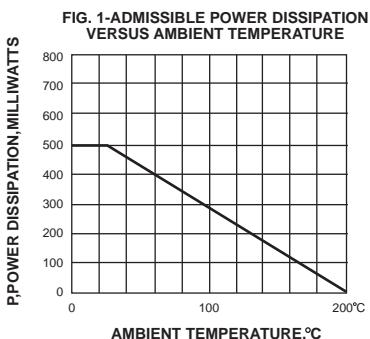
	SYMBOLS	1N4148	UNITS
Maximum repetitive peak reverse voltage	V _{RRM}	100	VOLTS
Maximum RMS voltage	V _{RMS}	75	VOLTS
Maximum average forward rectified current 0.375" (9.5mm) lead length at TA=25°C	I _(AV)	150	mAmps
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}	500	mAmps
Maximum instantaneous forward voltage at 10mA	V _F	1.0	Volts
Maximum DC reverse current TA=25°C V _R =75V at rated DC blocking voltage TA=100°C V _R =20V	I _R	5.0 50	µA
Maximum reverse recovery time (NOTE 1)	t _{rr}	4.0	ns
Typical junction capacitance (NOTE 2)	C _J	4.0	pF
Operating junction and storage temperature range	T _{J,T_{STG}}	-65 to +200	°C

NOTES:

1. Test condition: I_F=10mA, I_R=10mA, I_{rr}=1mA, V_R=6V, R_L=100Ω.

2. Measured at 1.0 MHz and applied reverse voltage of 4.0 volts

RATINGS AND CHARACTERISTIC CURVES 1N4148



Based on square wave currents. $T_J=25^\circ$ prior to surge.